

PTO/SB/08A (Substitute for form 1449/PTO)	Attorney Docket No.: 023-0030
	Application No.: 10/729,844
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	First Named Inventor: <i>En-Hsing Chen</i>
	Filing Date: December 5, 2003
	Group Art Unit: 2827
	Examiner Name: Mai, Son Luu
Sheet 1 of 1	Date Submitted: June 29, 2005

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

'Applicant's unique citation designation number (optional):

²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04.

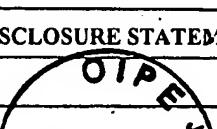
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⁴For Japanese patent documents, the indication of the year of the reign of the Emperor

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PTO/SB/08A (Substitute for form 1449/PTO)	Attorney Docket No.: 023-0030
	Application No.: 10/729,844
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	First Named Inventor: Roy E. Scheuerlein
	Filing Date: December 5, 2003
	Group Art Unit: 2818 - 2827
	Examiner Name: Son Luu Mai
Sheet 1 of 1	Date Submitted: June 1, 2005

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² <i>(if known)</i>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
<i>JM</i>		6,380,636	04-30-2002	Tatsukawa et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
Examiner Signature	SON MAI			Date Considered	7/8/05	

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PTO/SB/08B (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0030
		Application No.: 10/729,844
O P E R A T I O N INFORMATION DISCLOSURE STATEMENT BY APPLICANT APR 18 2005 PATENT & TRADEMARK OFFICE		First Named Inventor: En-Hsing Chen et al.
		Filing Date: December 5, 2003
		Group Art Unit: 2818-2827
Sheet 1 of 2		Examiner Name: Son Luu Mai
		Date Submitted: April 18, 2005

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
fm	AA	DURISETY, CHANDRA SEKHAR ACHARYULU, "Analysis and Characterization of Single-Poly Floating Gate Devices in 0.35um PDSOI Process", A Thesis Presented for the Master of Science Degree, The University of Tennessee, Knoxville, December 2002, pp. i-viii and 1-80.	/
fm	AB	EVANS, ROBERT J., ET AL., "Energy Consumption Modeling and Optimization for SRAM's," IEEE Journal of Solid-State Circuits, Vol. 30, No. 5, May 1995, pp. 571-579.	/
fm	AC	JUNG, TAE-SUNG, ET AL., "A 117-mm ² 3.3-V Only 128-Mb Multilevel NAND Flash Memory for Mass Storage Applications," IEEE Journal of Solid-State Circuits, Vol. 31, No. 11, November 1996, pp. 1575-1583.	/
fm	AD	KAWAGOE, HIROTO, ET AL., "Minimum Size ROM Structure Compatible with Silicon-Gate E/D MOS LSI," IEEE Journal of Solid-State Circuits, Vol. SC-11, No. 3, June 1976, pp. 360-364.	/
fm	AE	KIM, KYU-HYOUN, ET AL., "An 8-Bit-Resolution, 360- μ s Write Time Nonvolatile Analog Memory Based on Differentially Balanced Constant-Tunneling-Current Scheme (DBCS)," IEEE Journal of Solid-State Circuits, Vol. 33, No. 11, November 1998, pp. 1758-1762.	/
fm	AF	KIM, BYUNGCHEUL, ET AL., "A Scaled SONOS Single-Transistor Memory Cell for a High-Density NOR Structure with Common Source Lines," Journal of the Korean Physical Society, Vol. 41, No. 6, December 2002, pp. 945-948.	/
fm	AG	KIM, BYUNGCHEUL, ET AL., "Single Power Supply Operated and Highly Reliable SONOS EEPROMs," Journal of the Korean Physical Society, Vol. 40, No. 4, April 2002, pp. 642-644.	/
fm	AH	KITANO, YOSHITAKA, ET AL., "A 4-Mbit Full-Wafer ROM," IEEE Journal of Solid-State Circuits, Vol. SC-15, No. 4, August 1980, pp. 686-693.	/
fm	AI	LEE, YONG KYU, ET AL., "Multilevel Vertical-Channel SONOS Nonvolatile Memory on SOI," IEEE Electron Device Letters, Vol. 23, No. 11, November 2002, pp. 664-666.	/
fm	AJ	LIN, HORNG-CHIH, ET AL., "Ambipolar Schottky-Barrier TFTs," IEEE Transactions on Electron Devices, Vol. 49, No. 2, February 2002, pp. 264-270.	/
fm	AK	NAJEEB-UD-DIN ET AL., "Analysis of Floating Body Effects in Thin Film Conventional and Single Pocket SOI MOSFETs Using the GIDL Current Technique", IEEE Electron Device Letters, Vol. 23, No. 4, April 2002, pp. 209-211.	/
fm	AL	NISHIHARA, TOSHIYUKI, ET AL., "A Quasi-Matrix Ferroelectric Memory for Future Silicon Storage," IEEE Journal of Solid-State Circuits, Vol. 37, No. 11, November 2002, pp. 1479-1484.	/
fm	AM	PARK, KI-TAE, "Recent Non-Volatile Memory Device & Circuit Technology," Halo LSI Inc, (date unknown), 35 pages.	/
fm	AN	ROIZIN, YAKOV, ET AL., "Plasma-Induced Charging in Two Bit per Cell SONOS Memories," Tower Semiconductor Ltd., Migdal HaEmek 23105, Israel, (date unknown), 4 pages.	/

Examiner Signature	SON MAI	Date Considered	07/08/05
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.
(Continuation Sheet)		Filing Date: December 5, 2003
		Group Art Unit: 2818-2827
		Examiner Name: Son Luu Mai
Sheet 2 of 2		Date Submitted: April 18, 2005

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JM	AO	SHIN, JONGSHIN, ET AL., "A New Charge Pump Without Degradation in Threshold Voltage Due to Body Effect," IEEE Journal of Solid-State Circuits, Vol. 35, No. 8, August 2000, pp. 1227-1230.	/
JM	AP	STURM, J. C., ET AL., "Leakage Current Modeling of Series-Connected Thin Film Transistors," IEEE Transactions on Electron Devices, Vol. 42, No. 8, August 1995, pp. 1561-1563.	/
JM	AQ	SUGIBAYASHI, TADAHIKO, ET AL., "A 30-ns 256-Mb DRAM with a Multidivided Array Structure," IEEE Journal of Solid-State Circuits, Vol. 28, No. 11, November 1993, pp. 1092-1098.	/
JM	AR	SUH, KANG-DEOG, ET AL., "A 3.3 V 32 Mb NAND Flash Memory with Incremental Step Pulse Programming Scheme," IEEE Journal of Solid-State Circuits, Vol. 30, No. 11, November 1995, pp. 1149-1156.	/
JM	AS	TAKEUCHI, KEN, ET AL., "A Negative V _{th} Cell Architecture for Highly Scalable, Excellently Noise-Immune, and Highly Reliable NAND Flash Memories," IEEE Journal of Solid-State Circuits, Vol. 34, No. 5, May 1999, pp. 675-684.	/
JM	AT	THEAN, AARON, ET AL., "Flash memory: towards single-electronics," IEEE Potentials, October/November 2002, pp. 35-41.	
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	BD		
Examiner Signature		SON MAI	Date Considered
			07/08/05



Attorney Docket No.: 023-0030
Application No.: 10/729,844
Applicant(s): En-Hsing Chen et al.
Filing Date: December 5, 2003
Group Art Unit: 2818 2822
Date Submitted: April 18, 2005

LIST OF PENDING U. S. PATENT APPLICATIONS

The following pending U.S. patent applications are listed for consideration by the Examiner.

- JW*
- 1) U.S. Patent Application No. 10,729,865, filed December 5, 2003, entitled ‘NAND Memory Array Incorporating Multiple Series Selection Devices and Method for Operation of Same,’ naming inventors En-Hsing Chen, Andrew J. Walker, Roy E. Scheuerlein, Sucheta Nallamothu, Alper Ilkbahar, Luca G. Fasoli and James M. Cleeves.

JM

 - 2) U.S. Patent Application No. 10/729,843, filed December 5, 2003, entitled “Memory Array Incorporating Memory Cells Arranged in NAND Strings,” naming inventors Luca G. Fasoli, Roy E. Scheuerlein, En-Hsing Chen, Sucheta Nallamothu, Maitreyee Mahajani, and Andrew J. Walker.

EXAMINER
SON MAI

DATE CONSIDERED
07/06/05

Applicant(s) are providing a separate list of pending applications, pursuant to MPEP § 609III(D), to avoid publication of the application numbers on any patent that issues from the above-identified application. Applicant(s) request that the Examiner indicate consideration of the pending applications listed above in accordance with MPEP 609III(C)(2) and return a copy of this page with the next communication.

PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0030
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O I P E INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen et al.
APR 18 2005 PATENT & TRADEMARK OFFICE		Filing Date: December 5, 2003
		Group Art Unit: 2818-2827
		Examiner Name: Son Luu Mai
Sheet 1 of 5		Date Submitted: April 18, 2005

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
SL	AA	4,142,176	02-27-1979	Dozier	
SL	AB	4,543,594	09-24-1985	Mohsen et al.	
SL	AC	4,602,354	07-22-1986	Craycraft et al.	
SL	AD	4,868,616	09-19-1989	Johnson et al.	
SL	AE	5,197,027	03-23-1993	Challa	
SL	AF	5,301,144	04-05-1994	Kohno	
SL	AG	5,412,493	05-02-1995	Kunii et al.	
SL	AH	5,429,968	07-04-1995	Koyama	
SL	AI	5,473,563	12-05-1995	Suh et al.	
SL	AJ	5,568,421	10-22-1996	Aritome	
SL	AK	5,621,683	04-15-1997	Young	
SL	AL	5,644,533	07-01-1997	Lancaster et al.	
SL	AM	5,703,382	12-30-1997	Hack et al.	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ - Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
SL	AN	JA 62-142363	06-25-1987		
SL	AO	JA 62-155568	07-10-1987		
SL	AP	JA-2001-358237	12-26-2001		
SL	AQ	JA-2002-280467	09-27-2002		
Examiner Signature		SON SL		Date Considered	07/08/05

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(Continuation Sheet)		Filing Date: December 5, 2003
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Sheet 2 of 5		Date Submitted: April 18, 2005

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JM	AR	5,715,194	02-03-1998	Hu	
JM	AS	5,751,012	05-12-1998	Wolstenholme et al.	
JM	AT	5,814,853	09-29-1998	Chen	
JM	AU	5,835,396	11-10-1998	Zhang	
JM	AV	5,898,615	04-27-1999	Chida	
JM	AW	5,923,587	07-13-1999	Choi	
JM	AX	5,926,415	07-20-1999	Shin	
JM	AY	5,940,321	08-17-1999	Takeuchi et al.	
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Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ - Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
	BE					
	BF					
	BG					
	BH					
Examiner Signature	SON MAI			Date Considered	07/08/05	

PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0030
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(Continuation Sheet)		Filing Date: December 5, 2003
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Sheet 3 of 5		Date Submitted: April 18, 2005

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SL	BI	6,188,611 BI	02-13-2001	Endoh et al.	
SL	BJ	6,291,836	09-18-2001	Kramer et al.	
SL	BK	6,307,807 BI	10-23-2001	Sakui et al.	
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	BV					
	BW					
	BX					
	BY					
SL		SON MAI		Date Considered	07/08/05	

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(Continuation Sheet)		Filing Date: December 5, 2003
		Group Art Unit: 2818 - 2627
		Examiner Name: Son Luu Mai
Sheet 4 of 5		Date Submitted: April 18, 2005

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AM	BZ	6,515,888	02-04-2003	Johnson et al.	
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AM	CJ	6,856,572 B2	02-15-2005	Scheuerlein et al.	
AM	CK	6,859,410 B2	02-22-2005	Scheuerlein et al.	
AM	CL	US RE. 35,838	07-07-1998	Momodomi et al.	

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SL	CQ	US-2002/0021587 A1.	02-21-2002	Sakui et al	
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SL	CS	US-2003/0155582 A1	08-21-2003	Mahajani et al.	
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SL	CW	US-2004/045024 A1	07-29-2004	Chen et al.	
SL	CX	US-6,108,238	08-2000	Nakamura et al.	
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SL	DA	US-5,812,457	09-1998	Arase	
	DB				
	DC				

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	DF					
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